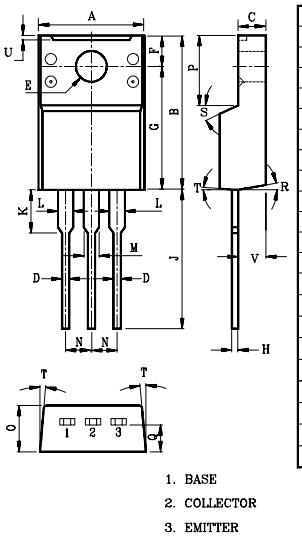
KTB1370

TRIPLE DIFFUSED PNP TRANSISTOR

HIGH CURRENT SWITCHING APPLICATIONS.
POWER AMPLIFIER APPLICATIONS.

FEATURES

- High Collector Current : I_C=-7A.
- Low Collector-Emitter Saturation Voltage.
  : $V_{CE(sat)}$=-0.5V(Max.) at I_C=-4A.



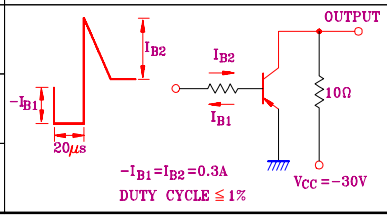
DIM	MILLIMETERS
A	10.30 MAX
B	15.30 MAX
C	2.70±0.30
D	0.85 MAX
E	ø3.20±0.20
F	3.00±0.30
G	12.30 MAX
H	0.75 MAX
J	13.60±0.50
K	3.90 MAX
L	1.20
M	1.30
N	2.54
O	4.50±0.20
P	6.80
Q	2.60±0.20
R	10°
S	25°
T	5°
U	0.5
V	2.60±0.15

TO-220IS

MAXIMUM RATINGS (Ta=25℃)

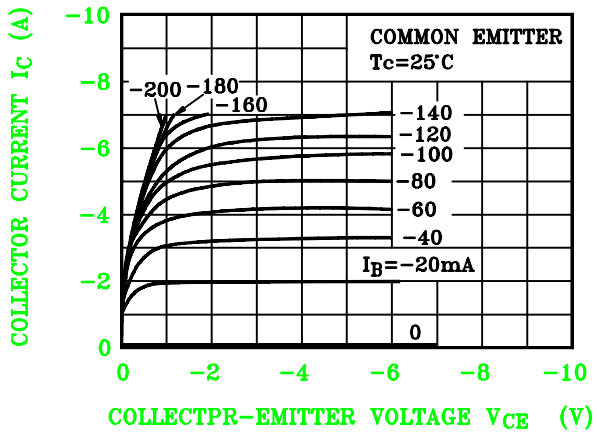
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-100	V
Collector-Emitter Voltage	V_{CEO}	-80	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-7	A
Base Current	I_B	-1	A
Collector Power Dissipation (Tc=25℃)	P_C	30	W
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55~150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃)

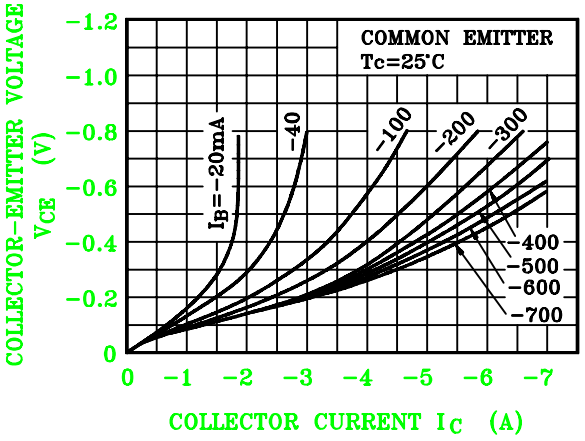
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	V_{CB}=-100V, I_E=0	-	-	-5	μA
Emitter Cut-off Current		I_{EBO}	V_{EB}=-5V, I_C=0	-	-	-5	μA
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	I_C=-50mA, I_B=0	-80	-	-	V
DC Current Gain		h_{FE}(1) (Note)	V_{CE}=-1V, I_C=-1A	70	-	240	
		h_{FE}(2)	V_{CE}=-1V, I_C=-4A	30	-	-	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	I_C=-4A, I_B=-0.4A	-	-0.3	-0.5	V
Base-Emitter Saturation Voltage		$V_{BE(sat)}$	I_C=-4A, I_B=-0.4A	-	-0.9	-1.4	V
Transition Frequency		f_T	V_{CE}=-4V, I_C=-1A	-	10	-	MHz
Collector Output Capacitance		C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz	-	250	-	pF
Switching Time	Turn-On Time	t_{on}		-	0.4	-	μS
	Storage Time	t_{stg}		-	2.5	-	
	Fall Time	t_f		-	0.5	-	

Note : h_{FE}(1) Classification O:70~140 , Y:120~240

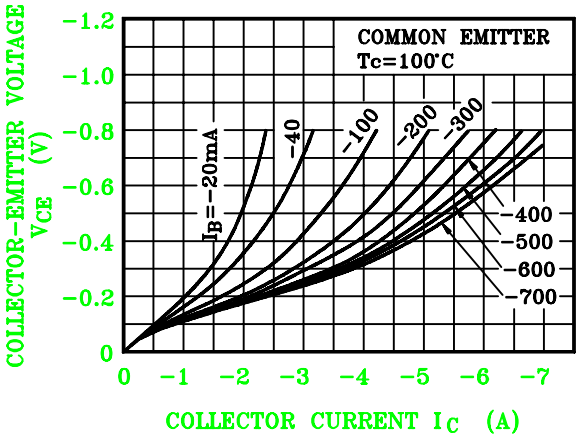
I_C – V_{CE}



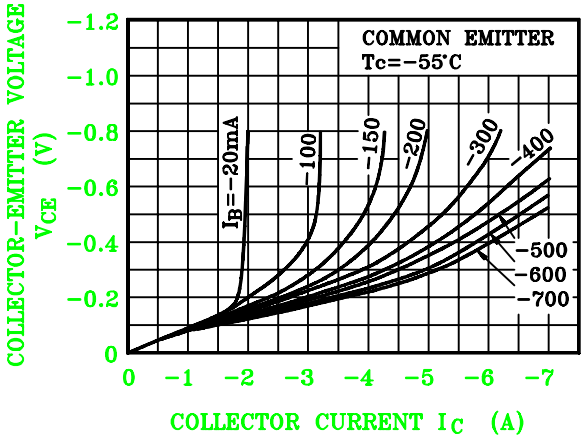
V_{CE} – I_C



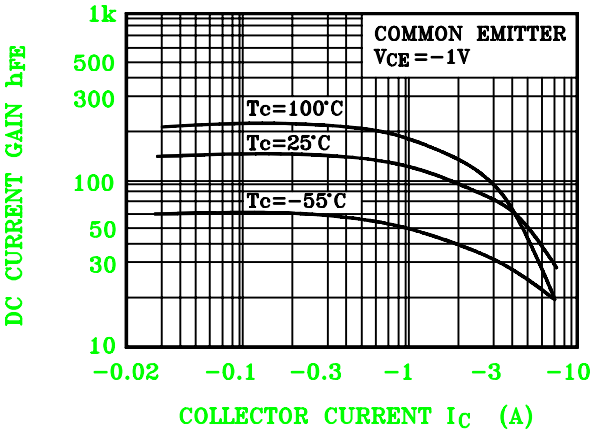
V_{CE} – I_C



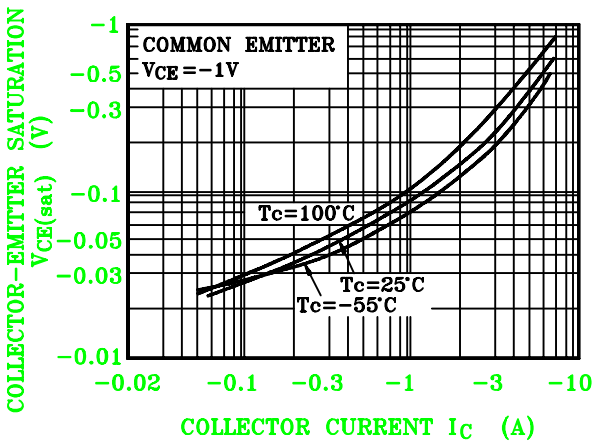
V_{CE} – I_C



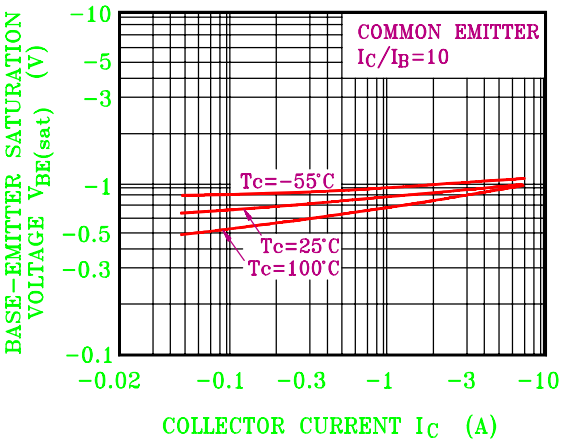
h_{FE} – I_C



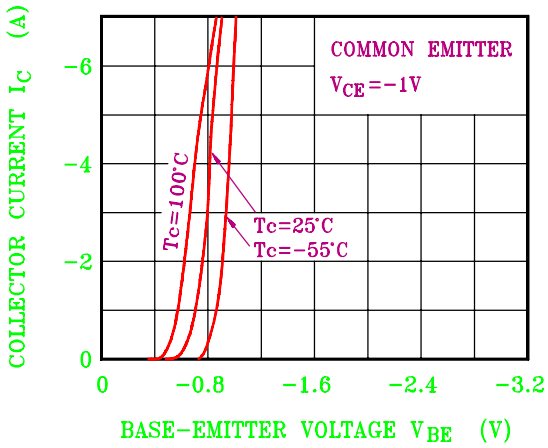
$V_{CE(sat)}$ – I_C



$V_{BE(sat)}$ – I_C



I_C – V_{BE}



SAFE OPERATING AREA